

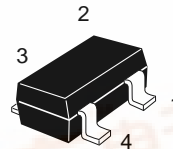
3SK229

GaAs Dual Gate MES FET
UHF TV Tuner RF Amplifier

Table 1 Absolute Maximum Ratings
(Ta = 25°C)

Item	Symbol	Rating	Unit
Drain to source voltage	V _{DS}	12	V
Gate 1 to source voltage	V _{G1S}	-6	V
Gate 2 to source voltage	V _{G2S}	-6	V
Drain current	I _D	50	mA
Channel power dissipation	P _{ch}	150	mW
Channel temperature	T _{ch}	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

MPAK-4



1. Source
2. Gate 1
3. Gate 2
4. Drain

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Drain to source cutoff current	I _{DSX}	—	—	50	μA	V _{DS} = 12 V, V _{G1S} = -4 V, V _{G2S} = 0
Gate 1 to source breakdown voltage	V _{(BR)G1SS}	-6	—	—	V	I _{G1} = -10 μA, V _{G2S} = V _{DS} = 0
Gate 2 to source breakdown voltage	V _{(BR)G2SS}	-6	—	—	V	I _{G2} = -10 μA, V _{G1S} = V _{DS} = 0
Gate 1 cutoff current	I _{G1SS}	—	—	-5	μA	V _{G1S} = -5 V, V _{G2S} = V _{DS} = 0
Gate 2 cutoff current	I _{G2SS}	—	—	-5	μA	V _{G2S} = -5 V, V _{G1S} = V _{DS} = 0
Drain current	I _{DSS}	15	25	40	mA	V _{DS} = 5 V, V _{G1S} = V _{G2S} = 0
Gate 1 to source cutoff voltage	V _{G1S(off)}	—	-1.3	-3.5	V	V _{DS} = 5 V, V _{G2S} = 0, I _D = 100 μA
Gate 2 to source cutoff voltage	V _{G2S(off)}	—	-1.3	-3.5	V	V _{DS} = 5 V, V _{G1S} = 0, I _D = 100 μA

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Table 2 Electrical Characteristics ($T_a = 25^\circ\text{C}$) (cont)

Item	Symbol	Min	Typ	Max	Unit	Test condition
Forward transfer admittance	$ y_{fs} $	20	34	—	mS	$V_{DS} = 5\text{ V}, V_{G2S} = 1\text{ V},$ $I_D = 10\text{ mA}, f = 1\text{ kHz}$
Input capacitance	C_{iss}	—	0.56	1.0	pF	$V_{DS} = 5\text{ V},$ $V_{G1S} = V_{G2S} = -4\text{ V},$ $f = 1\text{ MHz}$
Output capacitance	C_{oss}	—	0.36	0.6	pF	
Reverse transfer capacitance	C_{rss}	—	0.027	0.05	pF	
Power gain	PG	17	20	—	dB	$V_{DS} = 5\text{ V}, V_{G2S} = 1\text{ V},$ $I_D = 10\text{ mA}, f = 900\text{ MHz}$
Noise figure	NF	—	1.3	2.0	dB	

- Marking is "XS".
- See characteristic curve of 3SK228.

